

L1070-35M32

NIR Stem Type LED with High Output Power

L1070-35M32 is an InGaAsP LED mounted on a TO-18 stem with a spherical glass lens. It is designed for high output power use.

On forward bias, it emits a spectral band of radiation which peaks at 1070nm.

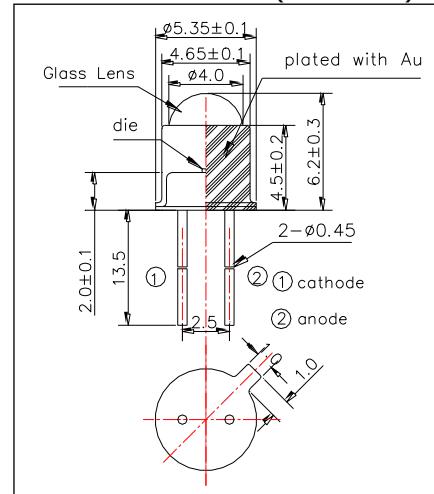
<Features>

- High Radiated Intensity
- High Reliability

<Specifications>

1. Product Name: NIR LED Lamp
2. Type Number: L1070-35M32
3. Chip:
 - Chip material: InGaAs/InP
 - Peak Wavelength: 1070nm
4. Package
 - Type: TO-18 Stem
 - Lens: Spherical Glass Lens
 - Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Power Dissipation	PD	130	mW
Forward Current	IF	100	mA
Pulse Forward Current*	IFP	1000	mA
Reverse Voltage	VR	3	V
Junction Temperature	Tj	100	°C
Thermal Resistance**	Rthja	260	K/W
Operating Temperature	TOPR	-30 ~ +80	°C
Storage Temperature	TSTG	-40 ~ +100	°C
Soldering Temperature***	TSOL	265	°C

* Duty=1% and Pulse Width=10μs.

** Junction - ambient, leads 7mm, soldered on PCB

*** Soldering condition must be completed within 3 second at 265°C.

Electro-Optical Characteristics						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=50mA		1.2	1.4	V
Reverse Current	IR	VR=5V			10	uA
Total Radiated Power*	PO	IF=50mA	0.8	1.8		mW
Radiant Intensity	IE	IF=50mA		1.9		mW/sr
Peak Wavelength	λP	IF=50mA	1050	1070	1100	nm
Half Width	Δλ	IF=50mA		100		nm
Viewing Half Angle	θ1/2	IF=50mA		±15		deg
Rise Time	tr	IF=50mA		30		ns
Fall Time	tr	IF=50mA		20		ns

* Measured by G8370-85

